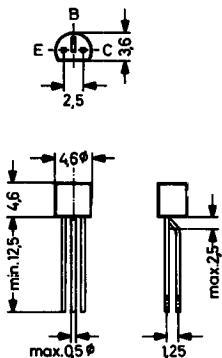


PNP Silicon Epitaxial Planar Transistors
with high cutoff frequency, for high speed switching



Plastic case $\approx$ JEDEC TO-92
TO-18 compatible
The case is impervious to light

Weight approximately 0.18 g
Dimensions in mm

Absolute Maximum Ratings

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	40	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	0.8	A
Power Dissipation at $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	625 ¹⁾	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^{\circ}\text{C}$

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

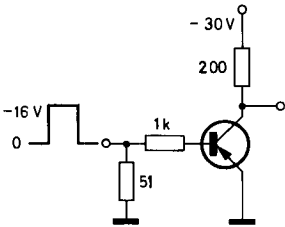


Fig. 1:
Test circuit for turn-on time

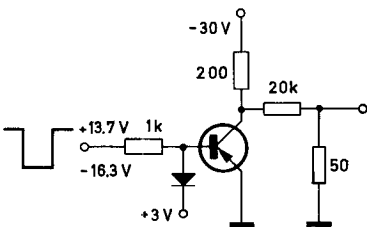


Fig. 2:
Test circuit for turn-off time

Characteristics at $T_{amb} = 25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE} = 10\text{ V}$, $-I_C = 0.1\text{ mA}$	2906 h_{FE}	20	—	—	—
	2907 h_{FE}	35	—	—	—
at $-V_{CE} = 10\text{ V}$, $-I_C = 1\text{ mA}$	2906 h_{FE}	25	—	—	—
	2907 h_{FE}	50	—	—	—
at $-V_{CE} = 10\text{ V}$, $-I_C = 10\text{ mA}$	2906 h_{FE}	35	—	—	—
	2907 h_{FE}	75	—	—	—
at $-V_{CE} = 10\text{ V}$, $-I_C = 150\text{ mA}$	2906 h_{FE}	40	—	120	—
	2907 h_{FE}	100	—	300	—
at $-V_{CE} = 10\text{ V}$, $-I_C = 0.5\text{ A}$	2906 h_{FE}	20	—	—	—
	2907 h_{FE}	30	—	—	—
Collector Saturation Voltage					
at $-I_C = 150\text{ mA}$, $-I_B = 15\text{ mA}$	$-V_{CEsat}$	—	—	0.4	V
at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{CEsat}$	—	—	1.6	V
Base Saturation Voltage					
at $-I_C = 150\text{ mA}$, $-I_B = 15\text{ mA}$	$-V_{BEsat}$	—	—	1.3	V
at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{BEsat}$	—	—	2.6	V
Collector Cutoff Current					
at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	—	—	20	nA
at $-V_{CB} = 50\text{ V}$, $T_{amb} = 125\text{ }^{\circ}\text{C}$	$-I_{CBO}$	—	—	20	μA
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	60	—	—	V
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	40	—	—	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	—	—	V
Gain Bandwidth Product at $-V_{CE} = 20\text{ V}$, $-I_C = 20\text{ mA}$, $f = 100\text{ MHz}$	f_T	200	—	—	MHz
Collector Base Capacitance at $-V_{CB} = 10\text{ V}$, $f = 100\text{ kHz}$	C_{CBO}	—	—	10	pF
Thermal Resistance Junction to Ambient	R_{thA}	—	—	200 ¹⁾	K/W
Turn-On Time (see Fig. 1) at $-I_{B1} = 15\text{ mA}$, $-I_C = 150\text{ mA}$	$t_d + t_r$	—	—	40	ns
Turn-Off Time (see Fig. 2) at $-I_{B1} = 15\text{ mA}$, $I_{B2} = 15\text{ mA}$, $-I_C = 150\text{ mA}$	$t_s + t_f$	—	—	250	ns
1) Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case					